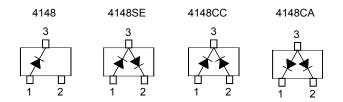
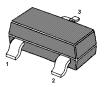


Silicon Epitaxial Planar Switching Diode





Marking Code: 5D MMBD4148 MMBD4148SE Marking Code: D4 MMBD4148CC Marking Code: D5 MMBD4148CA Marking Code: D6

SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

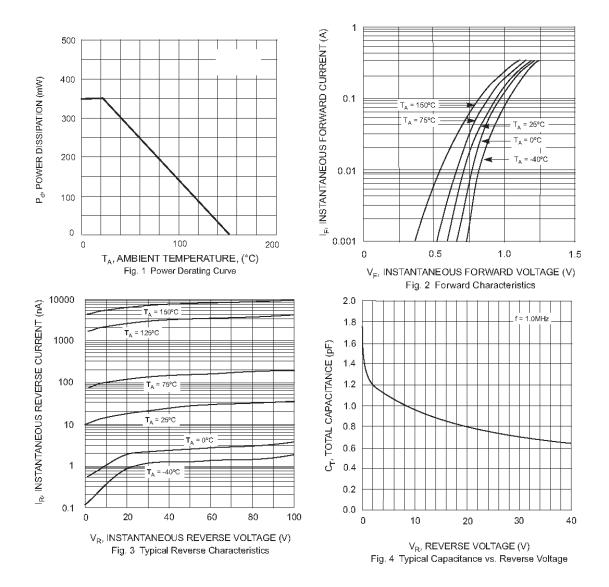
Parameter		Symbol	Value	Unit
Maximum Repetitive Reverse Voltage		V _{RRM}	100	V
Reverse Voltage		V_{R}	75	V
Average Rectified Forward Current		I _{F(AV)}	200	mA
DC Forward Current		I _{FM}	300	mA
Non-repetitive Peak Forward Surge Current	att=1s att=1µs	I _{FSM}	1 2	А
Total Device Dissipation		P _{tot}	350	mW
Operating Junction Temperature		Tj	150	°C
Storage Temperature Range		T _{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I _F = 10 mA	V _F	-	1	V
Reverse Breakdown Voltage at $I_R = 100 \ \mu A$ at $I_R = 5 \ \mu A$	V _{(BR)R}	100 75	-	V
Reverse Current at $V_R = 20 V$ at $V_R = 75 V$ at $V_R = 20 V$, $T_a = 150 °C$	I _R	- - -	25 5 50	nA μA μA
Reverse Recovery Time at I _F = 10 mA, V _R = 6 V, I _{RR} = 1 mA, R _L = 100 Ω	t _{rr}	-	4	ns
Total Capacitance at V _R = 0 V, f = 1 MHz	C _T	-	4	pF



Silicon Epitaxial Planar Switching Diode





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